

# New Wavelength Generation in T-Cavity Vertical-External-Cavity Surface-Emitting Lasers

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# Outline

**- Introduction to High Power VECSELs**

**- Single Chip Characteristics**

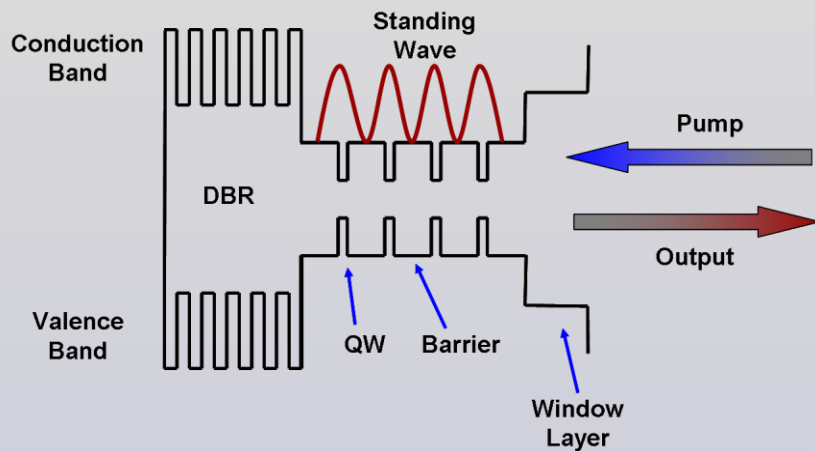
**- T-Cavity Configuration**

**- Sum Frequency Generation**

**- Difference Frequency Generation**

**- Concluding Remarks**

# Design of High Power VECSEL

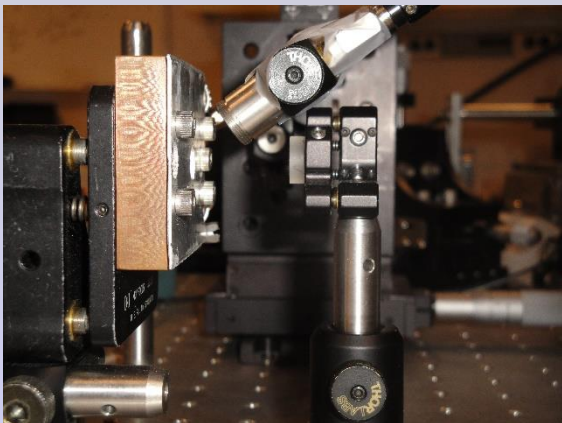
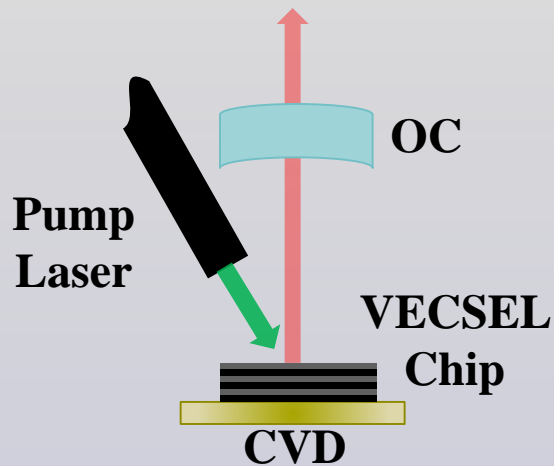


## Approach

- Large number of QWs with Resonant Periodic Gain
- Active region close to effective heat sink
- Thermal management by substrate removal, heat spreader approach

- InGaAs/GaAs /GaAsP strained compensated MQW
- Resonant periodic gain (RPG) MQW
- DBR on Chip
- Barrier Optical Pumping

# Linear Cavity Configuration



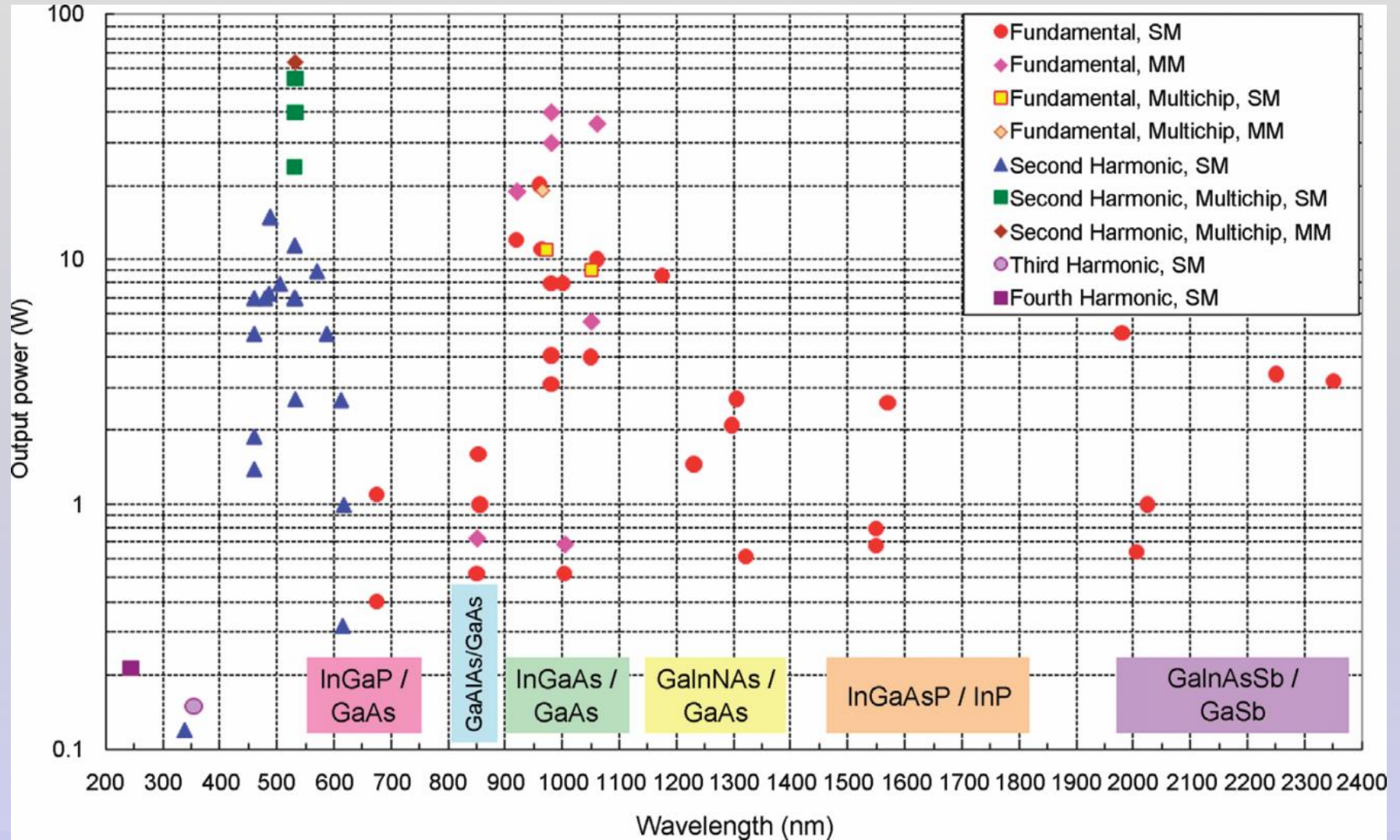
- High power and high beam quality (TEM<sub>00</sub>)

- Wavelength tolerant barrier pumping

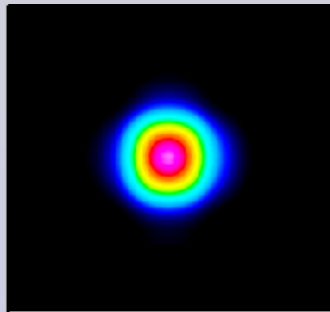
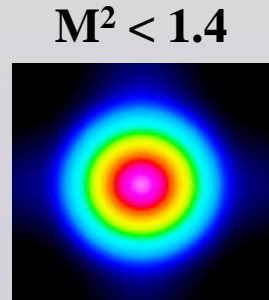
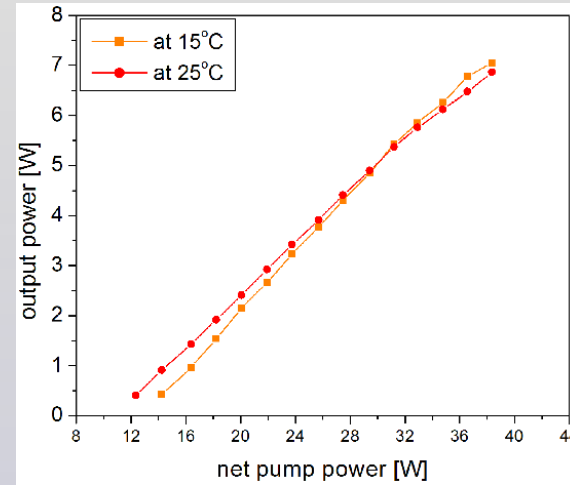
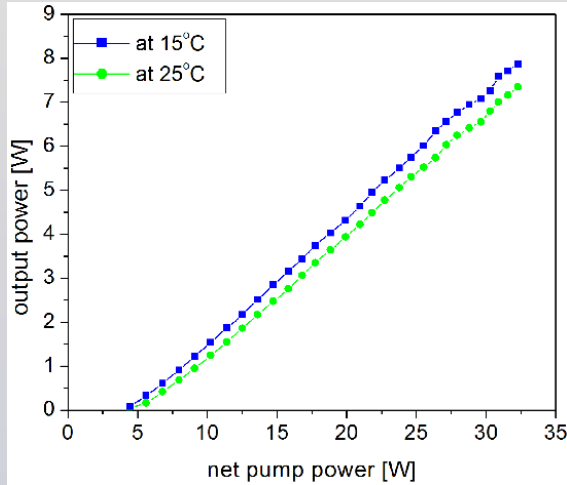
- Power scaling by increased beam diameter

- Access to intracavity radiation

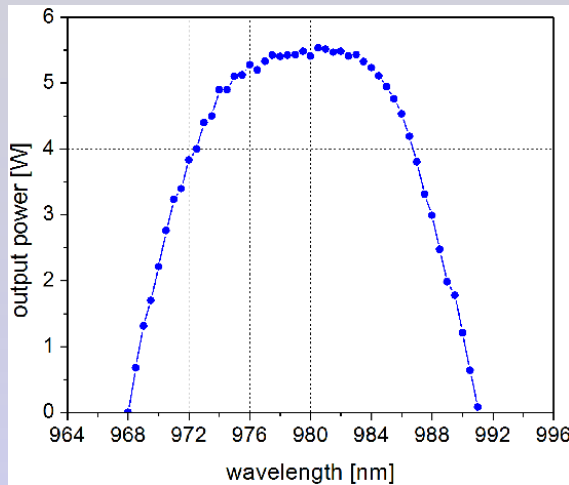
# VECSEL History and Progress



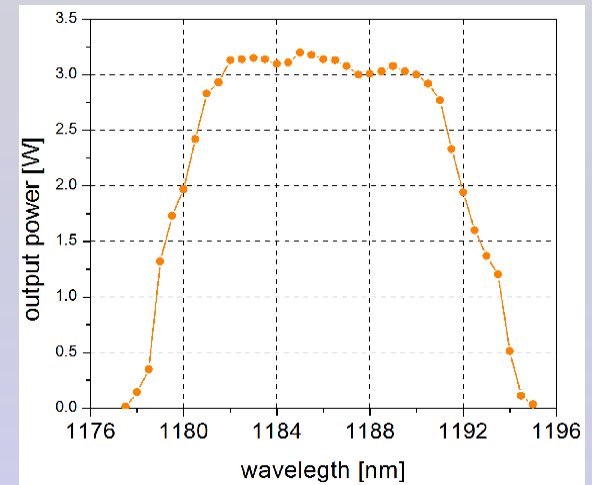
# Fundamental Performance



$M^2 < 1.3$



**980nm VECSEL**



**1180nm VECSEL**

# T-Cavity Configuration

## T-cavity Two-chip VECSEL:

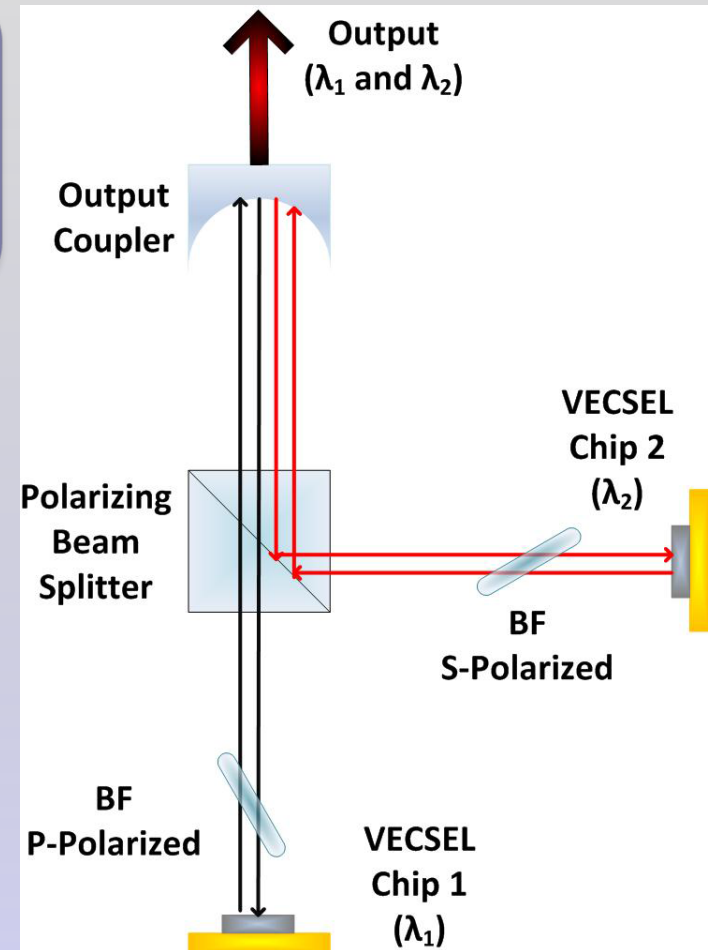
- TEM<sub>00</sub>, narrow linewidth for each wavelength
- Ease of wavelength tuning
- High intracavity intensity

### Chip 1: P-Polarized Cavity

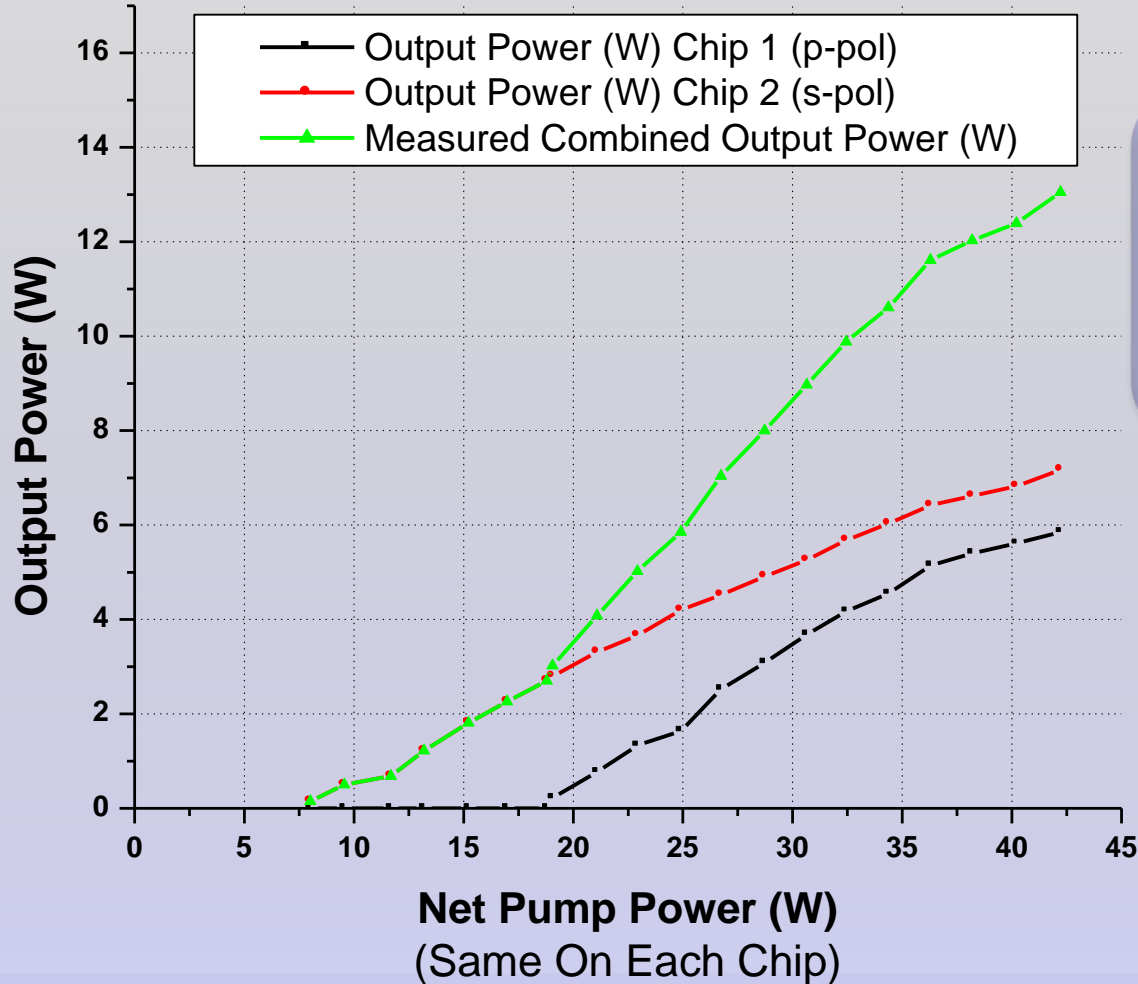
- Pump Spot Diameter ~ 500 $\mu$ m
- 1mm thick BF included in Cavity

### Chip 2: S-Polarized Cavity

- Pump Spot Diameter ~ 500 $\mu$ m
- 2mm thick BF included in Cavity



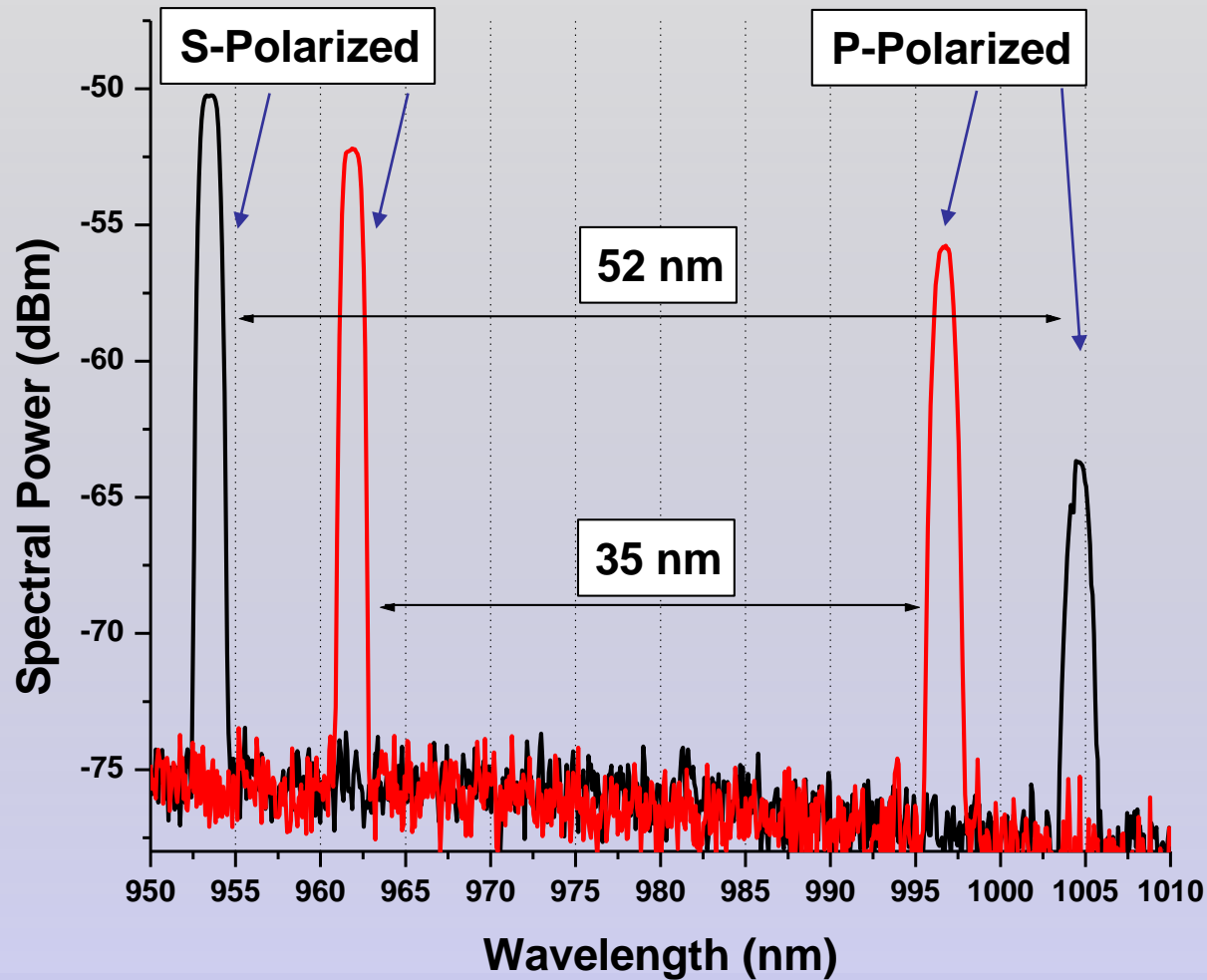
# Combined Output



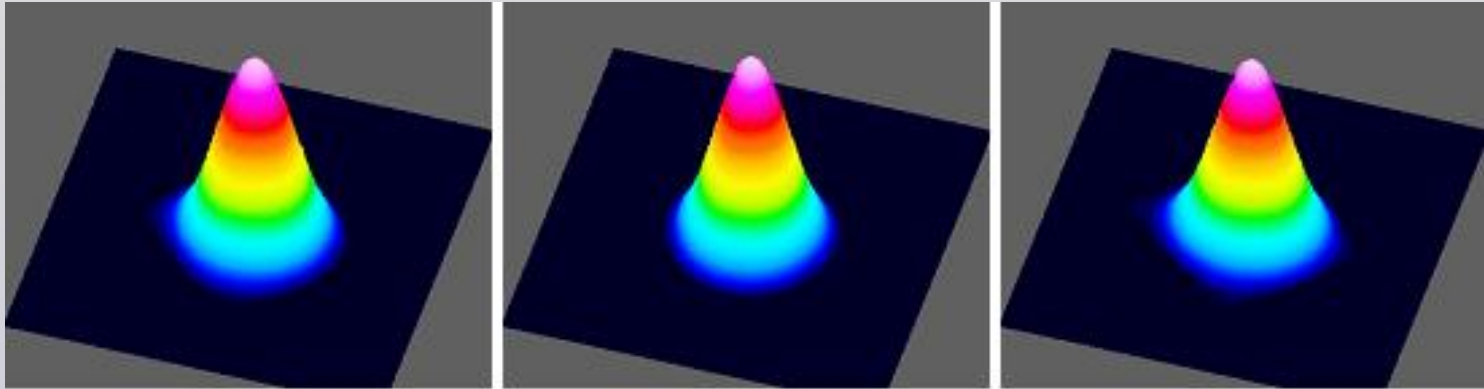
- Output measured for each cavity individually.
- Then the output was measured for the combined operation.



# Independent Tuning of Each Wavelength



# Output Profiles of Collinear Operation



A)

B)

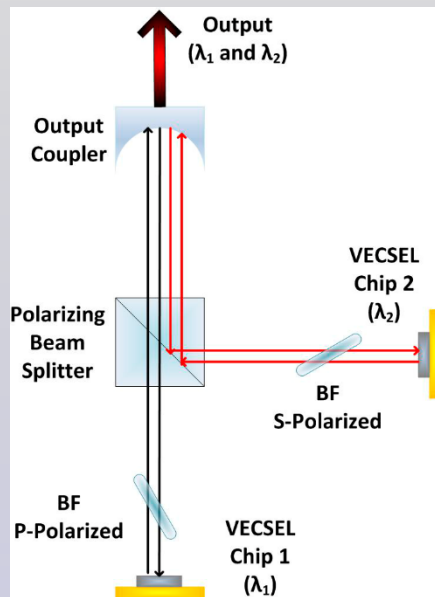
C)

Measured outputs beam profiles

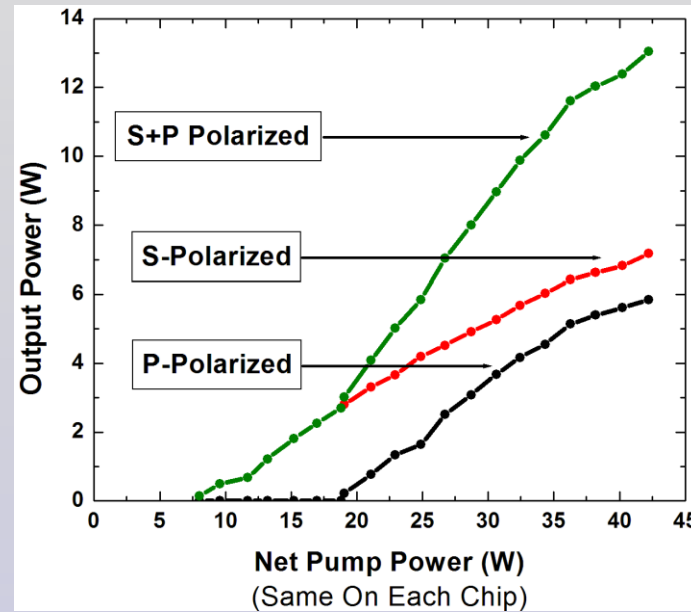
- a) P-polarized beam profile.
- b) S-polarized beam profile.
- c) Combined S and P output beam profile.

# T-Cavity Configuration Summary

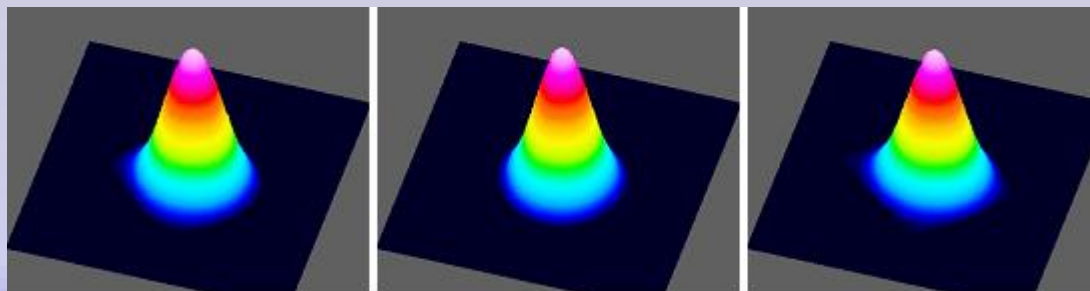
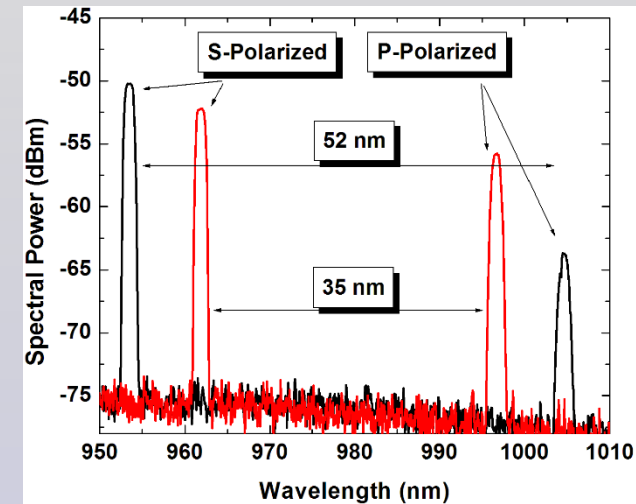
## Cavity Design



## Total Output is Sum of Both Cavities

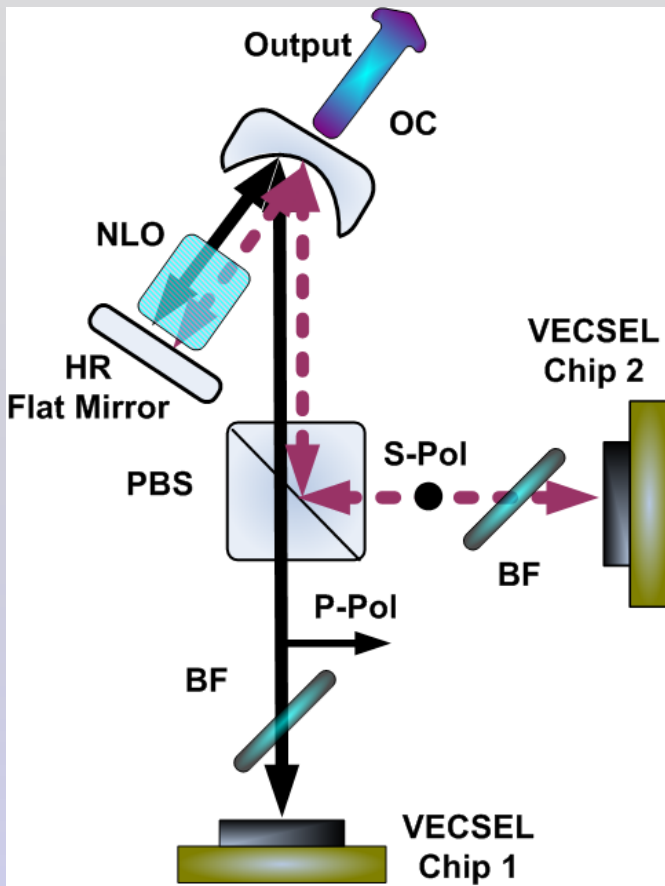


## Individual Tuning of Each Wavelength

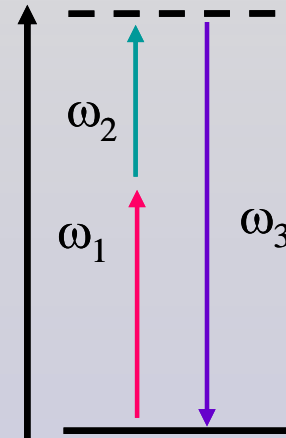


Excellent Beam  
Overlap is  
Demonstrated

# SFG and DFG



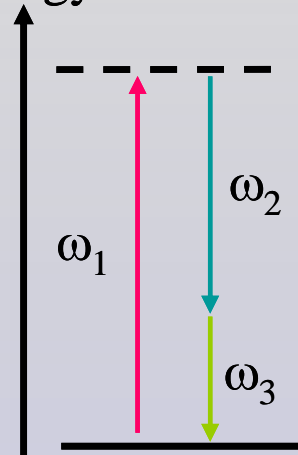
Energy



SFG

$$\omega_3 = \omega_1 + \omega_2$$

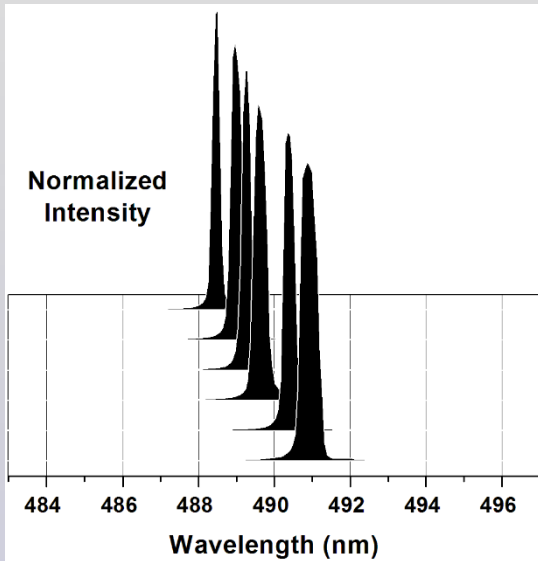
Energy



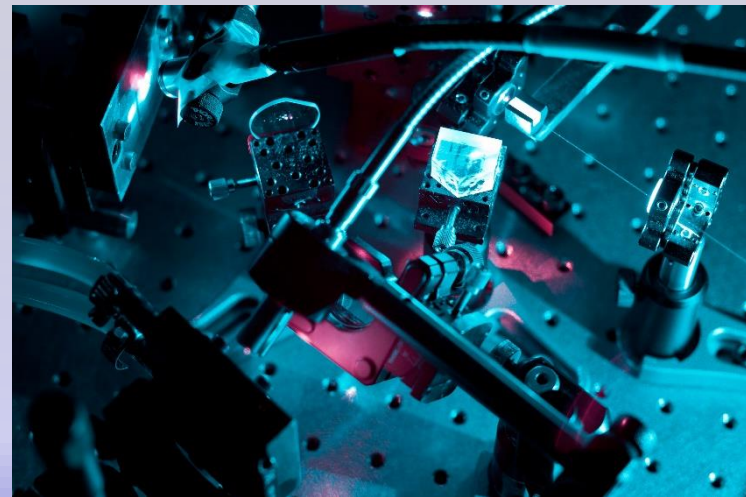
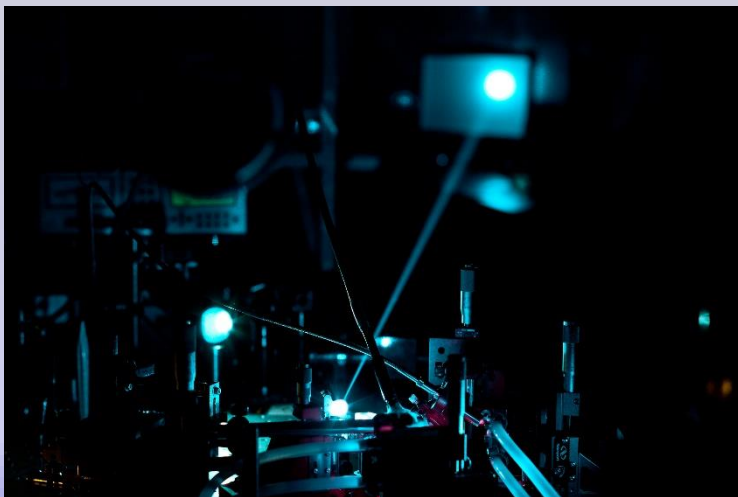
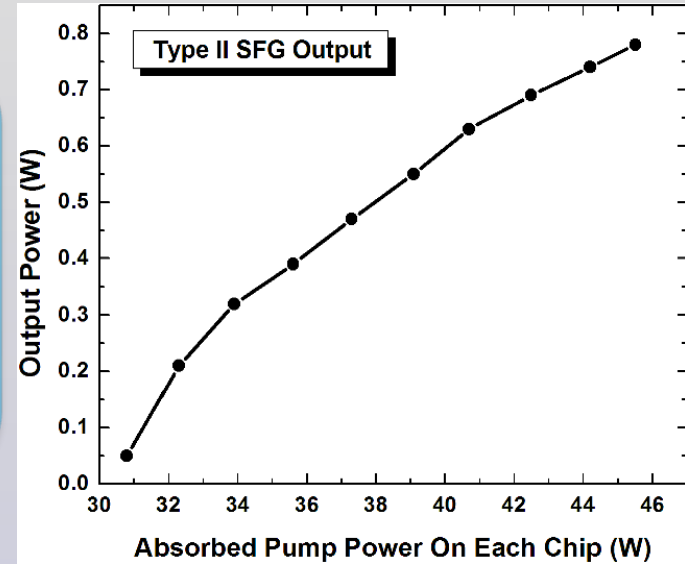
DFG

$$\omega_3 = \omega_1 - \omega_2$$

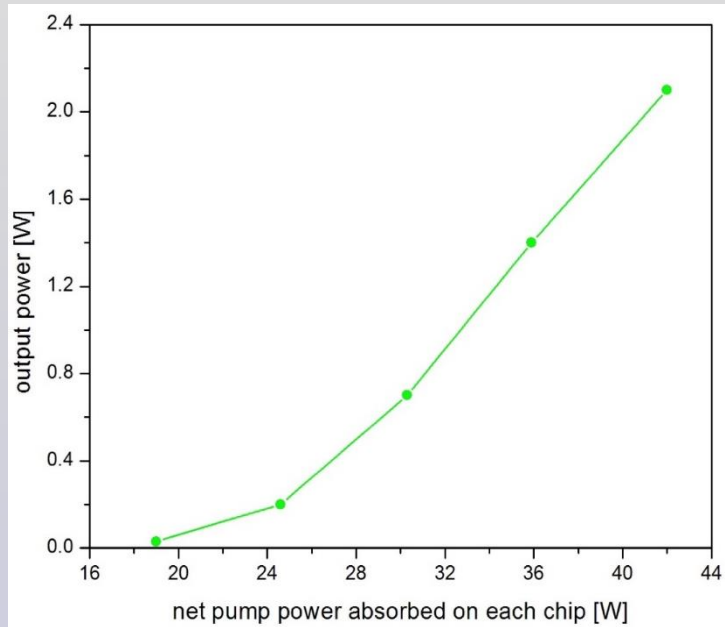
# Type II SFG in T-Cavity



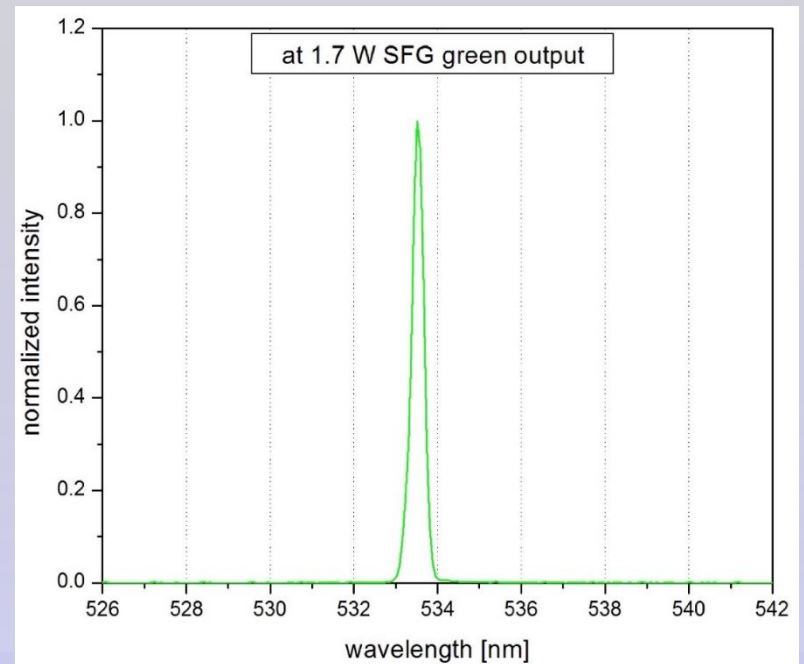
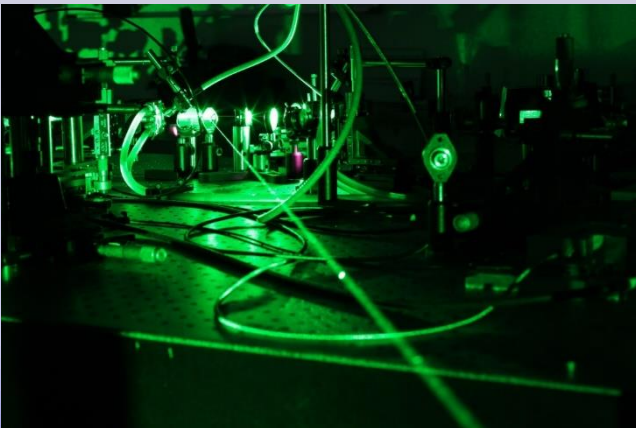
- Combine two VECSEL chips with similar 980nm outputs
- Tunable type II blue



# Type II Green Output

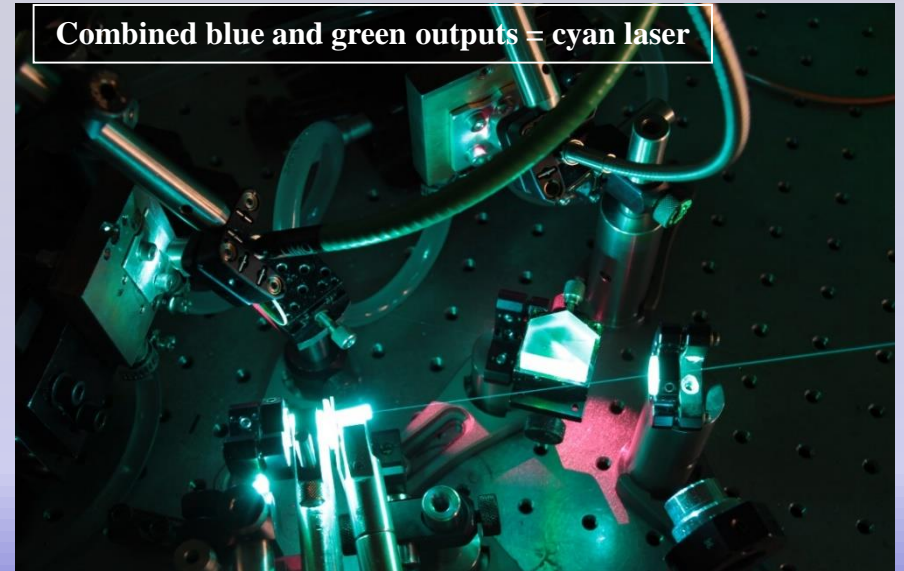
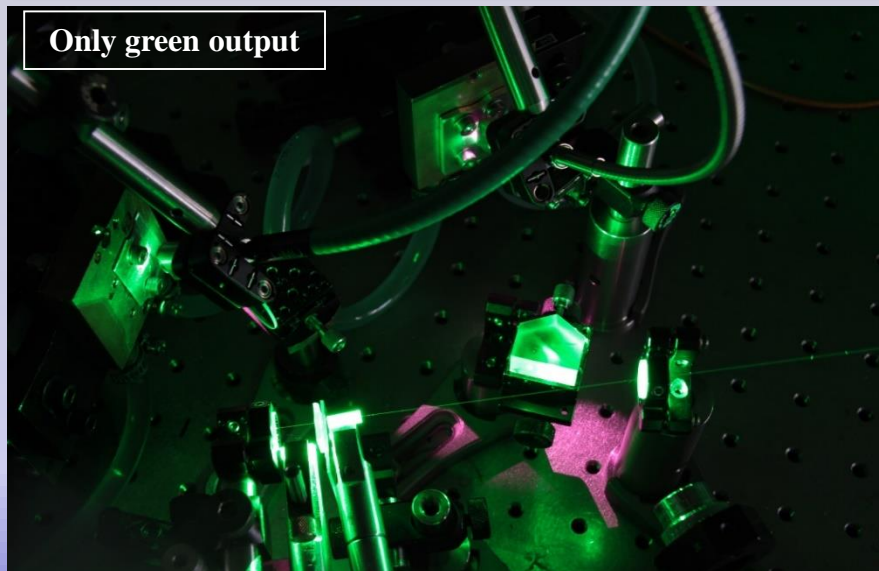
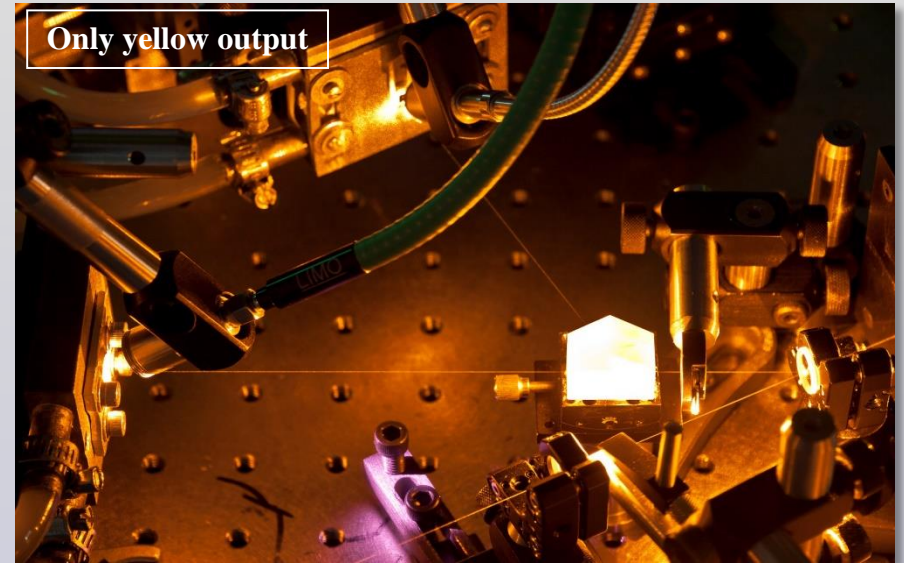
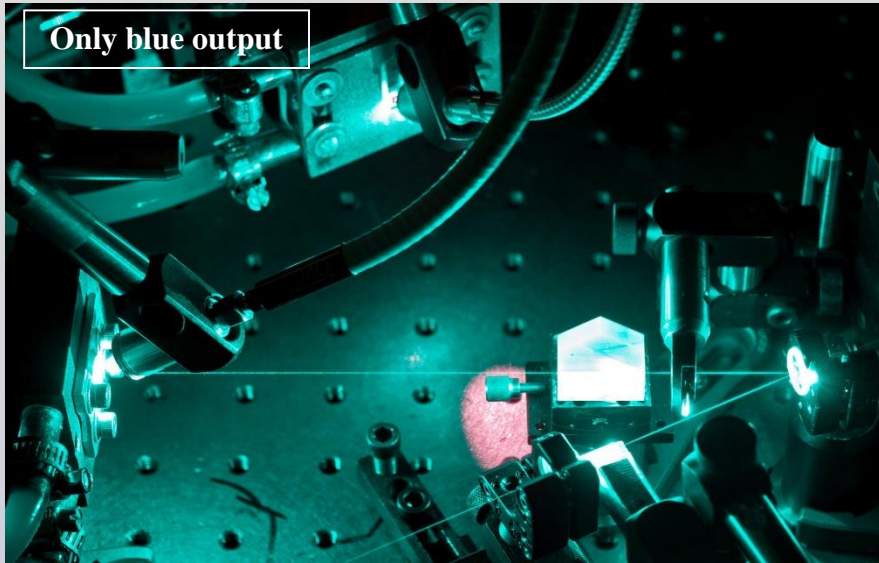


Can mix 1180nm and 980nm VECSEL chips to generate green outputs

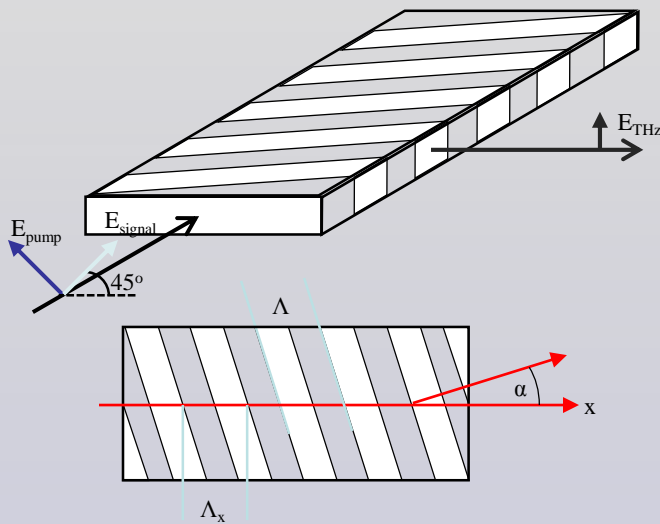




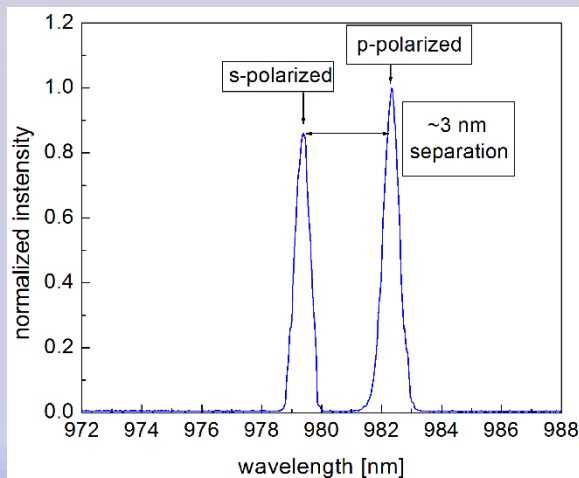
# Multiple Color Generation



# THz by Type II DFG



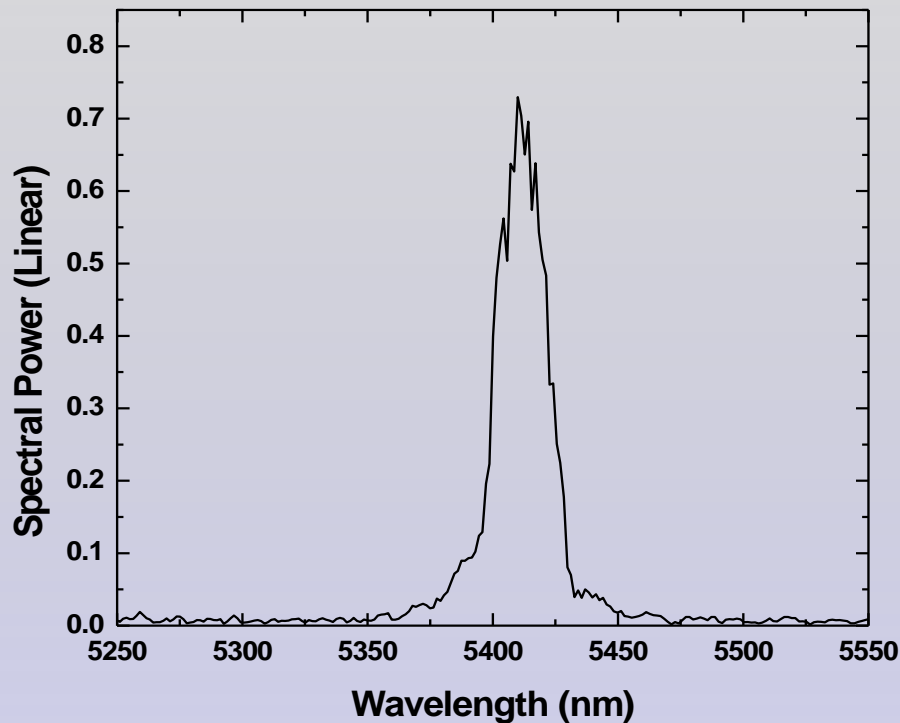
PPLN with tilted poling period  
for perpendicular THz extraction



Fundamental separation  $\sim 3$  nm  
for  $\sim 1$  THz output



# Mid-IR by Type II DFG



Same configuration for green SFG yields mid-IR via DFG

Fundamentals at  $\sim 968\text{nm}$  and  $\sim 1179\text{nm}$  produced output at  $\sim 5400\text{nm}$

# Concluding Remarks

- **VECSELs offer a flexible platform for a wide range of fundamental lasing wavelengths**
- **Can be a viable and affordable alternative for widely tunable Visible and IR high-power sources**
- **Intracavity access can allow for new operating features**
- **Two-chip T-cavity can provide efficient SFG and DFG pulsed operation**